RENESAS

R2A20112ASP

Critical Conduction Mode Interleaved PFC Control IC

R03DS0047EJ0100 Rev.1.00 Jul 21, 2011

Description

The R2A20112A controls a boost converter to provide an active power factor correction.

The R2A20112A adopts critical conduction mode for power factor correction and realizes high efficiency and a low switching noise by zero current switching.

Interleaving function improves ripple current on input or output capacitor by 180 degrees phase shift.

Soft-star, the feedback loop short detection, two mode over-voltage-protection, over-current-protection, Over current ON/OFF timer protection for boost Diode short and slave ZCD open detection are built in the R2A20112A, and can constitute a power supply system of high reliability with few external parts.

Features

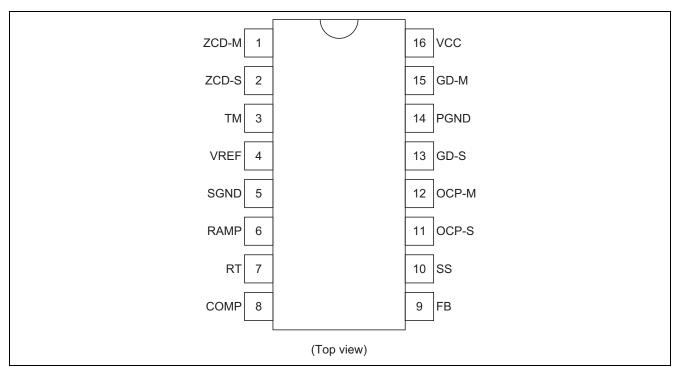
- Absolute Maximum Ratings
 - Supply voltage Vcc: 24 V
 - Operating junction temperature Tjopr: -40 to +150°C
- Electrical Characteristics
 - VREF output voltage Vref: $5.0 V \pm 1.5\%$
 - UVLO operation start voltage Vuvlh: 10.5 V \pm 0.7 V
 - UVLO operation shutdown voltage Vuvll: 9.3 V \pm 0.5 V
 - UVLO hysteresis voltage Hysuvl: $1.2 \text{ V} \pm 0.5 \text{ V}$
- Functions
 - Boost converter control with critical conduction mode
 - Interleaving control
 - Soft start function for the reference voltage of Error Amp
 - Two mode PFC output Over-voltage-protection
 Mode1: Dynamic OVP corresponding to a voltage rise by dynamic load change.
 Mode2: Static OVP corresponding to over-voltage in stable.
 - PFC output Dynamic-under-voltage-protection (DUVP)
 - Feedback loop open/short detection
 - Master and Slave independence over-current-protection
 - 280 µs restart timer
 - Slave ZCD signal open detection
 - Over current ON/OFF timer protection for boost Diode short
- Package
 - Pb-free SOP-16

Ordering Information

Part No.	Package Name	Package Code	Package Abbreviation	Taping Abbreviation (Quantity)
R2A20112ASPW0	FP-16DAV	PRSP0016DH-B	SP	W (2,000 pcs/reel)



Pin Arrangement

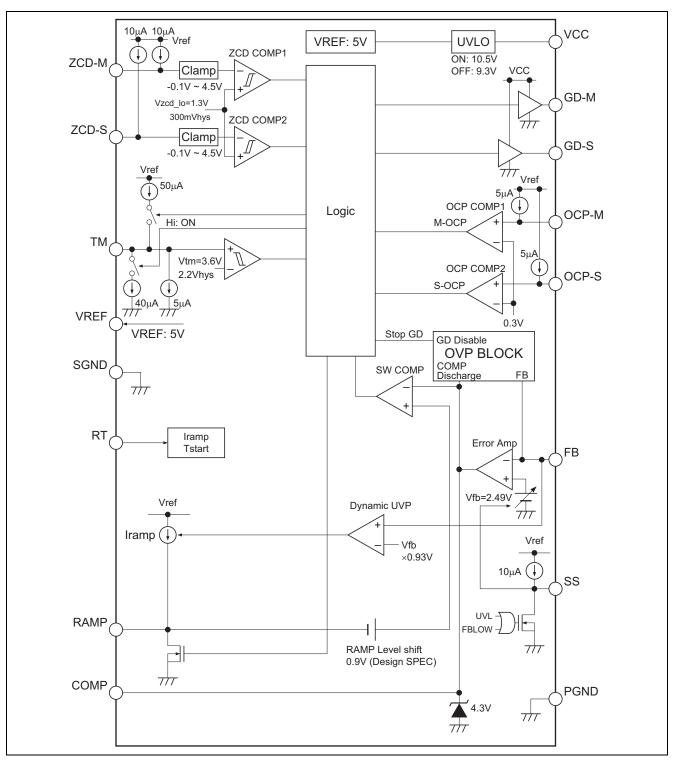


Pin Functions

Pin No.	Pin Name	Function			
1	ZCD-M	Master converter zero current detection input terminal			
2	ZCD-S	Slave converter zero current detection input terminal			
3	ТМ	Over current ON/OFF timer protection terminal			
4	VREF	Reference voltage output terminal			
5	SGND	Signal Ground			
6	RAMP	Ramp waveform setting terminal			
7	RT	Oscillator frequency setting terminal			
8	COMP	Error amplifier output terminal			
9	FB	Error amplifier input terminal			
10	SS	Soft start time setting terminal			
11	OCP-S	Slave converter overcurrent detection terminal			
12	OCP-M	Master converter overcurrent detection terminal			
13	GD-S	Slave converter Power MOSFET drive terminal			
14	PGND	Power Ground			
15	GD-M	Master converter Power MOSFET drive terminal			
16	VCC	Supply voltage terminal			



Block Diagram





Absolute Maximum Ratings

				$(Ta = 25^{\circ}C)$
Item	Symbol	Ratings	Unit	Notes
Supply voltage	VCC	-0.3 to +24	V	
GD terminal peak current	lpk-gd	-300 mA +1200		3
GD terminal DC current	ldc-gd	-15 +60	mA	
ZCD terminal current	eurrent Izcd +3 -3		mA	
RT terminal current	Irt	-200	μΑ	4
Vref terminal current	Iref	-5	mA	
Vref terminal load capacitor	Cref min	1000	pF	
	Cref max	1	μF	
COMP terminal current	Icomp	±1	mA	
Terminal voltage	Vt-group1	-0.3 to Vcc	V	5
	Vt-group2	–0.3 to Vref	V	6
Vref terminal voltage	Vt-ref	-0.3 to Vref + 0.3	V	
OCP terminal voltage	Vt-ocp	*-1 to Vref	V	7
Power dissipation	Pt	1	W	8
Operating junction temperature	Tj-opr	-40 to +150	°C	
Storage temperature	Tstg	-55 to +150	°C	

Notes: 1. Rated voltages are with reference to the PGND terminal.

2. For rated currents, inflow to the IC is indicated by (+), and outflow by (-).

3. Shows the transient current when driving a capacitive load.

4. RT terminal's resistor is fixed 33 k Ω to GND.

- 5. This is the rated voltage for the following pins: Nothing
- 6. This is the rated voltage for the following pins: FB, SS, RAMP, TM

7. Minus value is peak voltage. Do not impress the DC voltage of the minus.

8. θja = 120°C/W

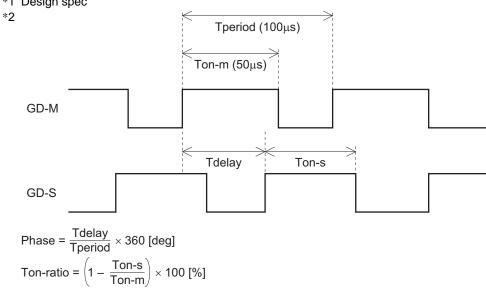
This value is a thing mounting on 40×40 (thickness: 1.6 mm) [mm²], a glass epoxy board of wiring density 10%.



Electrical Characteristics

Item		Symbol	Min	Тур	Max	Unit	Test Conditions	
Supply	UVLO turn-on threshold	Vuvlh	9.8	10.5	11.2	V		
	UVLO turn-off threshold	Vuvll	8.8	9.3	9.8	V		
	UVLO hysteresis	Hysuvl	0.7	1.2	1.7	V		
	Standby current	Istby	—	85	170	μA	VCC = 8.9 V	
	Operating current	Icc	—	4.2	6.3	mA		
VREF	Output voltage	Vref	4.925	5.00	5.075	V	Isource = -1 mA	
	Line regulation	Vref-line	_	5	20	mV	Isource = -1 mA Vcc = 10 V to 24 V	
	Load regulation	Vref-load	_	5	20	mV	Isource = -1 mA to -5 mA	
	Temperature stability	dVref	—	±80		ppm/°C	Ta = -40 to +125°C * ¹	
Error	Feedback voltage	Vfb	2.452	2.490	2.528	V	FB-COMP short	
amplifier	Input bias current	lfb	-0.5	-0.3	-0.1	μA	Measured pin: FB FB = 3 V * ¹	
	Open loop gain	Av	—	60	_	dB	*1	
	Upper clamp voltage	Vclamp-comp	4.2	4.3	4.4	V	FB = 2.0 V	
	Low voltage	VI-comp	_	0.1	0.3	V	FB = 3.0 V	
	Source current	Isrc-comp	—	-120	—	μΑ	FB = 1.5 V COMP = 2.5 V * ¹	
	Sink current	Isnk-comp	_	330	_	μA	FB = 3.5 V COMP = 2.5 V	
	Transconductance	gm	120	200	290	μS	FB = 2.45V ↔ 2.55 V COMP = 2.5 V	
Ramp	RAMP charge current at DUVP disable condition	lc-ramp1	-60	-50	-40	μA	FB = 2.4 V	
	RAMP charge current at DUVP enable condition	lc-ramp2	-32	-25	-18	μΑ	FB = 2 V	
	RAMP discharge current	ld-ramp	7	15	29	mA	RAMP = 1 V	
	Low voltage	VI-ramp	—	17	200	mV	lsink = 100 μA	
Slave	Phase delay	Phase	160	180	200	deg	FB = 2.5 V, COMP = 2 V	
control	On time ratio	Ton-ratio	0	_	5	%	* ^{1, 2}	

Notes: *1 Design spec



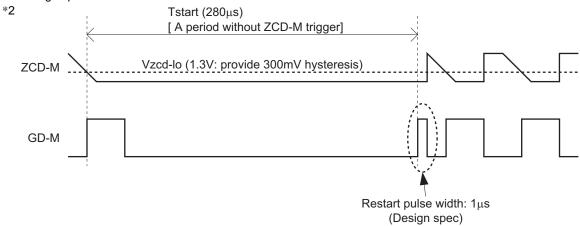


Electrical Characteristics (cont.)

 $(Ta = 25^{\circ}C, VCC = 12 V, RT = 33 k\Omega, RAMP = 820 pF, TM = 2.2 \mu F, SS = 1.0 \mu F, OCP = GND)$

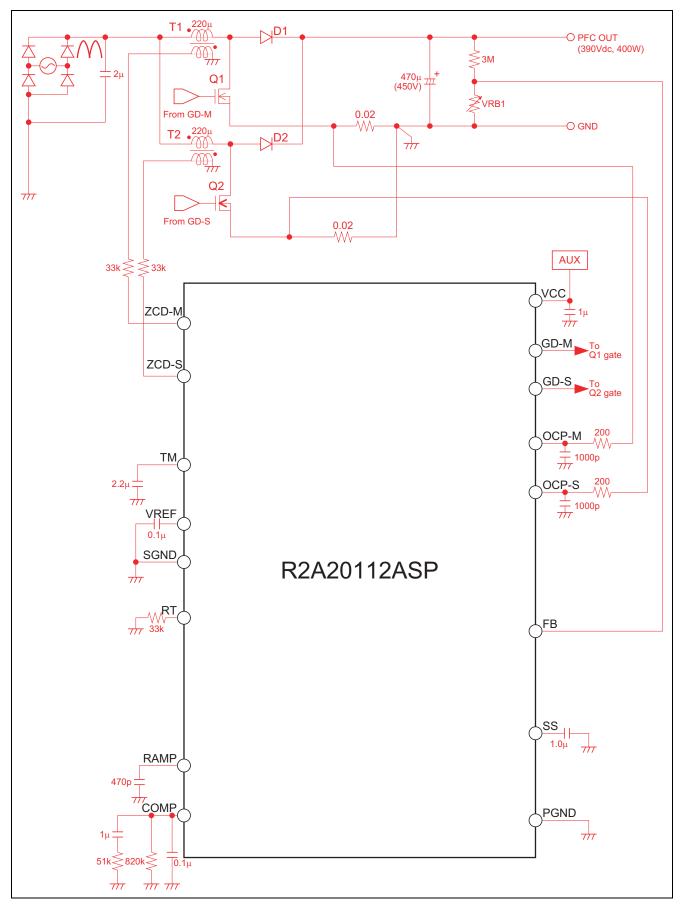
Item		Symbol	Min	Тур	Max	Unit	Test Conditions
Gate drive (GD-M &	Gate drive rise time	tr-gd	_	20	100	ns	FB-COMP short 90% CL = 100 pF 10%
GD-S)	Gate drive fall time	tf-gd	_	5	30	ns	FB-COMP short 90% CL = 100 pF 10%
	Gate drive low voltage	Vol1-gd	—	0.02	0.1	V	Isink = 2 mA
		Vol2-gd	—	0.01	0.2	V	Isink = 1 mA, VCC = 5 V
	Gate drive high voltage	Voh-gd	11.5	11.9	—	V	Isource = $-2 \text{ mA} *^1$
Over current	OCP threshold voltage	Vocp	0.27	0.30	0.33	V	
protection (OCP-M & OCP-S	OCP source current	Іоср	-10	-5	-2.5	μA	OCP = 0 V
ON/OFF timer	ON/OFF timer threshold voltage	Vtm	3.52	3.6	3.68	V	
protection for	ON/OFF timer hysteresis	Hys-tm	2.1	2.2	2.3	V	
Boost diode	Charge current	Isrc-tm	-54	-45	-36	μΑ	TM = 2 V, OCP-M = 1 V
short	Discharge current at TM disable condition	lsnk-tm1	36	45	54	μΑ	TM = 2 V
	Discharge current at TM enable condition	lsnk-tm2	4.2	5	5.8	μΑ	TM = 5 V to 2 V
PFC output abnormality	Dynamic OVP threshold voltage	Vdovp	Vfb× 1.035	Vfb× 1.050	Vfb× 1.065	V	COMP = 2.5 V
protection	Static OVP threshold voltage	Vsovp	Vfb× 1.075	Vfb× 1.090	Vfb× 1.105	V	COMP = 2.5 V
	Static OVP hysteresis	Hys-sovp	50	100	150	mV	COMP = 2.5 V
	Dynamic UVP threshold voltage	Vduvp	_	Vfb× 0.930	Vfb× 0.950	V	COMP = 2.5 V * ¹
	FB low detect threshold voltage	Vfblow	0.45	0.50	0.55	V	COMP = 2.5 V
	FB low detect hysteresis	Hysfblow	0.16	0.20	0.24	V	COMP = 2.5 V
Zero current	Upper clamp voltage	Vzcdh	4.0	4.5	5.0	V	Isource = -3 mA
detector	Lower clamp voltage	Vzcdl	-0.5	-0.1	0.4	V	Isink = 3 mA
(ZCD-M &	ZCD low threshold voltage	Vzcd-lo	0.9	1.3	1.6	V	*1
ZCD-S)	ZCD hysteresis	Hyszcd	130	300	410	mV	*1
	Input bias current	Izcd	-14	-10	-6	μΑ	1.2 V < Vzcd < 2.5 V
ZCD-S open detector	Slave ZCD open detect delay time	tzcds	—	100	—	ms	ZCD-S: OPEN Gate drive 10 kHz * ¹
Soft start	Charge current	lc-ss	-14	-10	-6	μΑ	SS = 3 V, FB = 1 V
Restart	Restart time delay	Tstart	210	280	350	μS	ZCD-M = 10 kΩ to GND ZCD-S = 10 kΩ to GND $*^2$

Notes: *1 Design spec

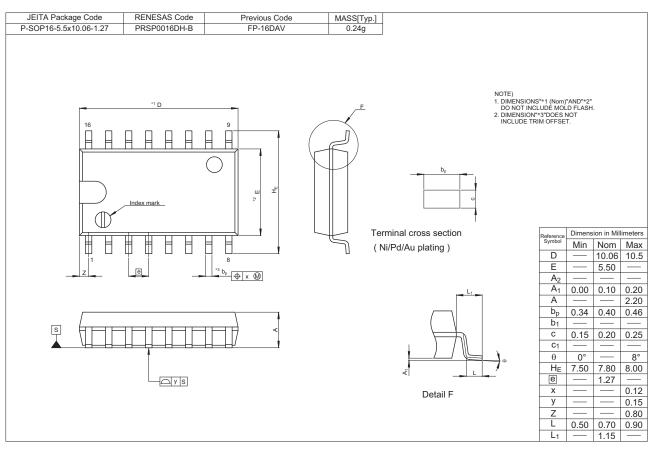




System Diagram



Package Dimensions





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